

## ABSTRACT

To provide a magnetic memory cell that is capable of efficiently changing the magnetization directions of magneto-sensitive layers. A magnetic memory cell comprises an annular magnetic layer 4a through which extends a write bit line 5a that generates a magnetic field, and a TMR film S20a configured so as to include: a first magneto-sensitive layer 14a, a magnetization direction of which is changed by the magnetic field in the annular magnetic layer 4a; and a magnetoresistive effect revealing body 20a disposed on a surface of the first magneto-sensitive layer 14a so that an electric current flows in a direction perpendicular to a laminating surface of the laminate, and the first magneto-sensitive layer 14a has a thickness thereof set in a range of not less than 0.5 nm to not more than 40 nm.